

FORM PTO-1449 (Rev. 2-32)	<b>U.S. DEPARTMENT OF COMMERCE</b> <b>PATENT AND TRADEMARK OFFICE</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>		
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	<b>ATTY. DOCKET NO.</b> TI-33969	<b>SERIAL NO.</b> <u>New 10/618473</u>
	<b>APPLICANT:</b> Xiaowei Deng, et al.	
	<b>FILING DATE:</b> July 11, 2003	<b>GROUP:</b> <u>TBD 2824</u>

## **U.S. PATENT DOCUMENTS**

## FOREIGN PATENT DOCUMENTS


**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**

*VTN* Koji Nii, et al., "A 90 nm Low Power 32K-Byte Embedded SRAM with Gate Leakage Suppression Circuit for Mobile Applications", Symposium on VLSI Circuits, 2003.

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